CR08AS

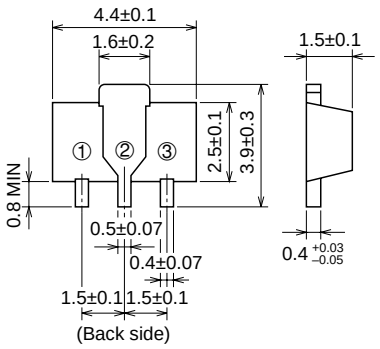
LOW POWER USE

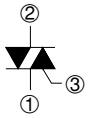
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

CR08AS

- $I_{T\ (AV)}$ 0.8A
- V_{DRM} 400V/600V
- I_{GT} 100μA

OUTLINE DRAWING Dimensions in mm





① T_1 TERMINAL
② T_2 TERMINAL
③ GATE TERMINAL

SOT-89

APPLICATION

Solid state relay, strobe flasher, ignitor, hybrid IC

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8 (marked "AD")	12 (marked "AF")	
V_{RRM}	Repetitive peak reverse voltage	400	600	V
V_{RSM}	Non-repetitive peak reverse voltage	500	720	V
$V_{R\ (DC)}$	DC reverse voltage	320	480	V
V_{DRM}	Repetitive peak off-state voltage *1	400	600	V
$V_{D\ (DC)}$	DC off-state voltage *1	320	480	V

Symbol	Parameter	Conditions	Ratings	Unit
$I_{T\ (RMS)}$	RMS on-state current		1.26	A
$I_{T\ (AV)}$	Average on-state current	Commercial frequency, sine half wave, 180° conduction, T_a=51°C*2	0.8	A
I_{TSM}	Surge on-state current	60Hz sine half wave 1 full cycle, peak value, non-repetitive	10	A
I^2t	I^2t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	0.42	A^2s
P_{GM}	Peak gate power dissipation		0.5	W
$P_{G\ (AV)}$	Average gate power dissipation		0.1	W
V_{FGM}	Peak gate forward voltage		6	V
V_{RGM}	Peak gate reverse voltage		6	V
I_{FGM}	Peak gate forward current		0.3	A
T_j	Junction temperature		–40 ~ +125	°C
T_{stg}	Storage temperature		–40 ~ +125	°C
—	Weight	Typical value	48	mg

*1. With Gate-to-cathode resistance R_{GK}=1kΩ

MITSUBISHI ELECTRIC

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LOW POWER USE
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ELECTRICAL CHARACTERISTICS

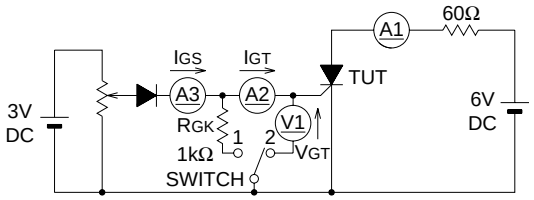
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{RRM}	Repetitive peak reverse current	T_j=125°C, V_{RRM} applied, R_{GK}=1kΩ	—	—	0.5	mA
I_{DRM}	Repetitive peak off-state current	T_j=125°C, V_{DRM} applied, R_{GK}=1kΩ	—	—	0.5	mA
V_{TM}	On-state voltage	T_a=25°C, I_{TM}=2.5A, instantaneous value	—	—	1.5	V
V_{GT}	Gate trigger voltage	T_a=25°C, V_D=6V, I_T=0.1A *4	—	—	0.8	V
V_{GD}	Gate non-trigger voltage	T_j=125°C, V_D=1/2V_{DRM}, R_{GK}=1kΩ	0.2	—	—	V
I_{GT}	Gate trigger current	T_j=25°C, V_D=6V, I_T=0.1A *4	1	—	100*3	μA
I_H	Holding current	T_j=25°C, V_D=12V, R_{GK}=1kΩ	—	1.5	3	mA
$R_{th\ (j-a)}$	Thermal resistance	Junction to ambient *2	—	—	65	°C/W

*2. Soldering with ceramic plate (25mm × 25mm × t0.7).
*3. If special values of I_{GT} are required, choose at least two items from those listed in the table below. (Example: AB, BC)

Item	A	B	C
I_{GT} (μA)	1 ~ 30	20 ~ 50	40 ~ 100

The above values do not include the current flowing through the 1kΩ resistance between the gate and cathode.

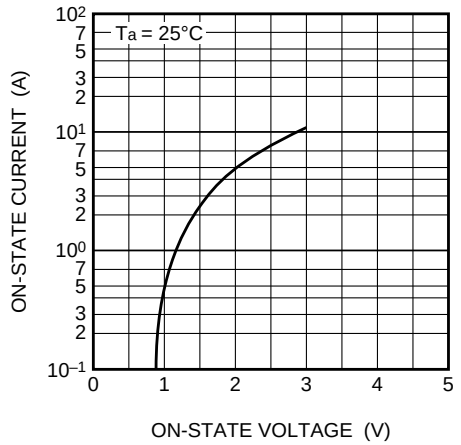
*4. I_{GT}, V_{GT} measurement circuit.



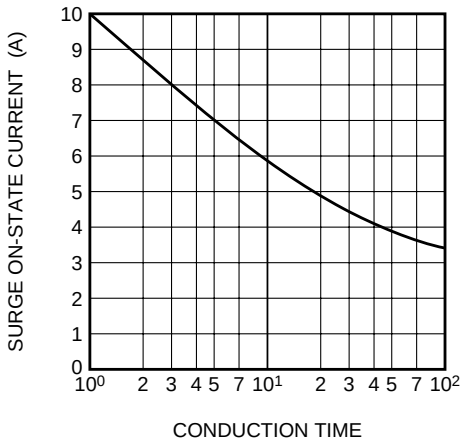
SWITCH 1 : I_{GT} measurement
SWITCH 2 : V_{GT} measurement
(Inner resistance of voltage meter is about 1kΩ)

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS



RATED SURGE ON-STATE CURRENT



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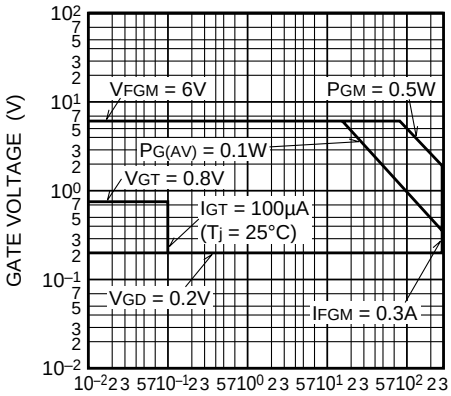
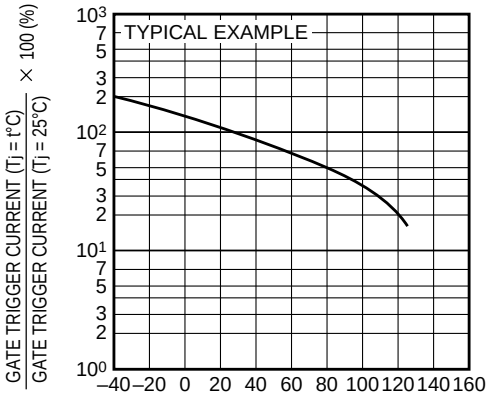
LOW POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

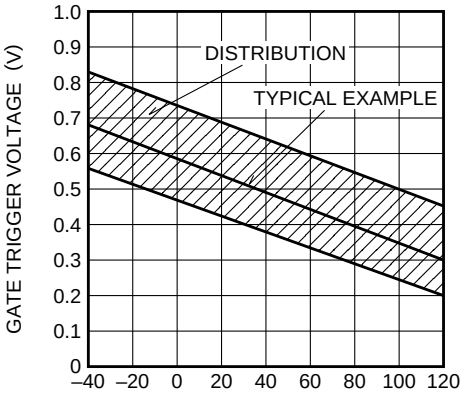
GATE CHARACTERISTICS



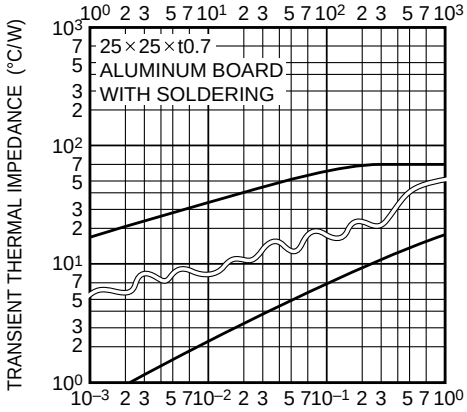
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



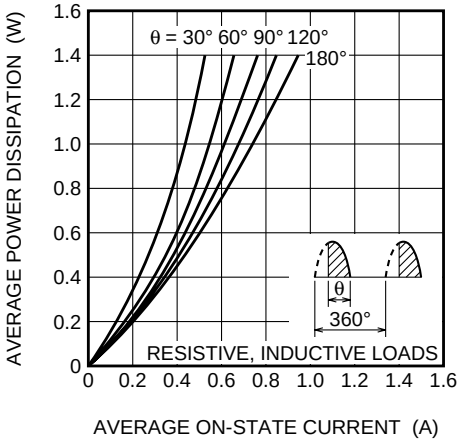
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



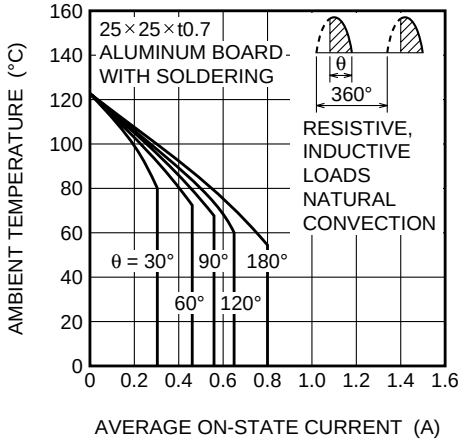
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)



MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE HALF WAVE)



ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



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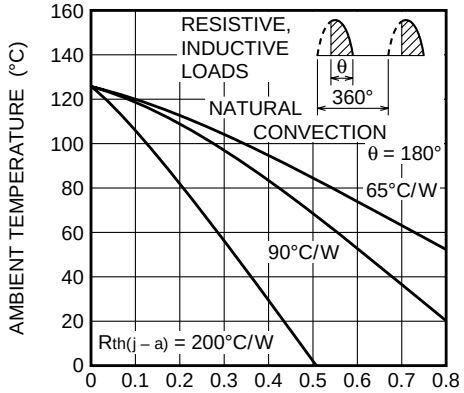
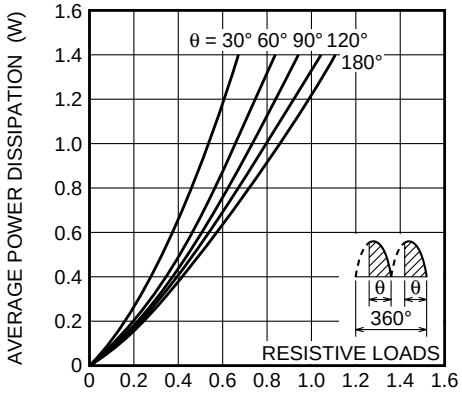
LOW POWER USE
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

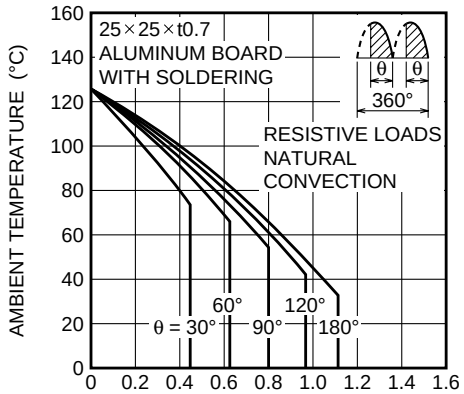
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



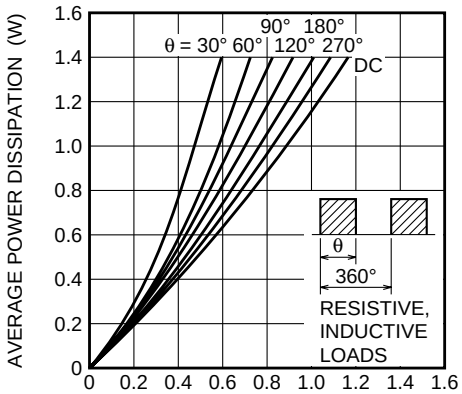
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE FULL WAVE)



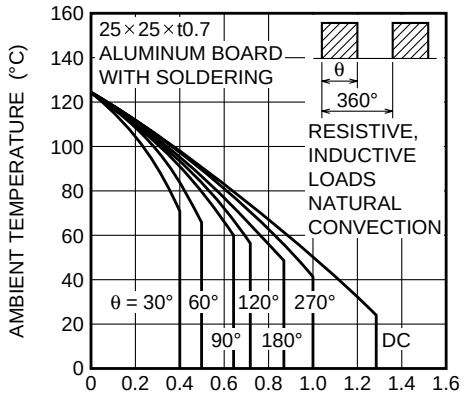
ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)



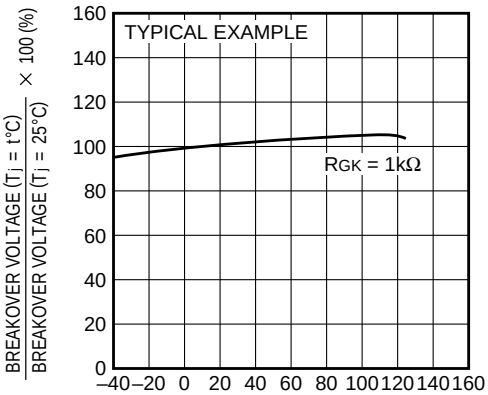
MAXIMUM AVERAGE POWER DISSIPATION (RECTANGULAR WAVE)



ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)



BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE



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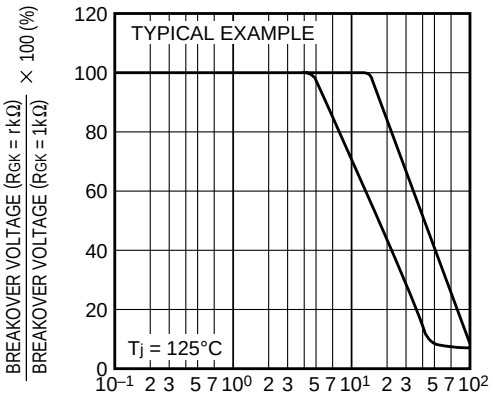
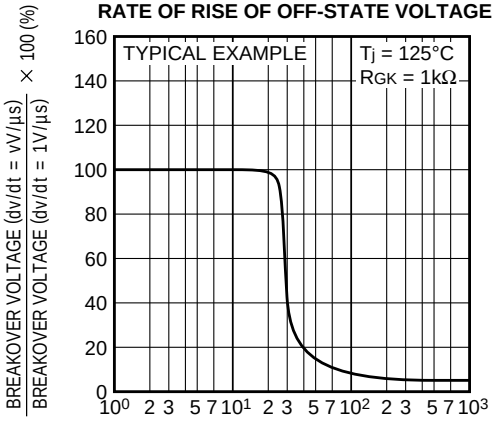
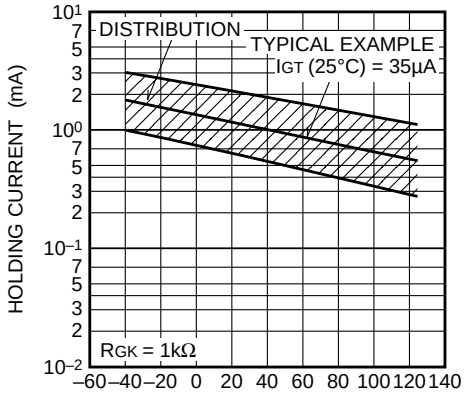
BREAKOVER VOLTAGE VS. GATE TO CATHODE RESISTANCE



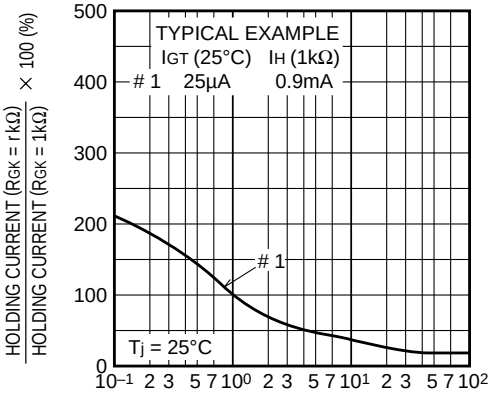
BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



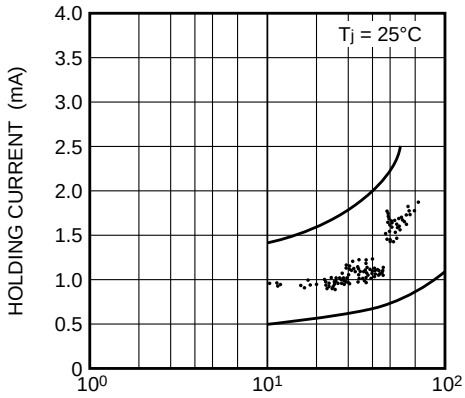
HOLDING CURRENT VS. JUNCTION TEMPERATURE



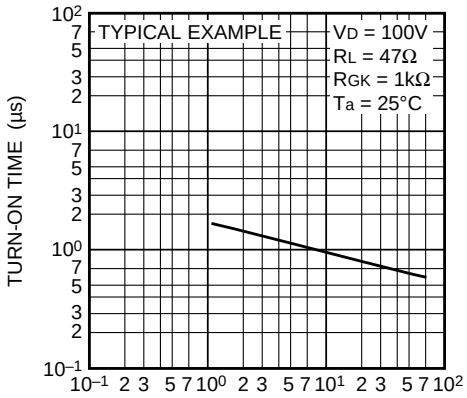
HOLDING CURRENT VS. GATE TO CATHODE RESISTANCE



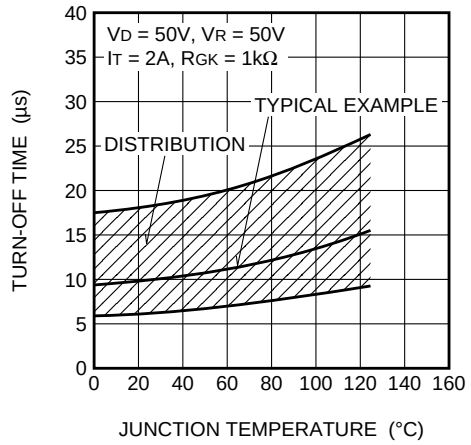
HOLDING CURRENT VS. GATE TRIGGER CURRENT



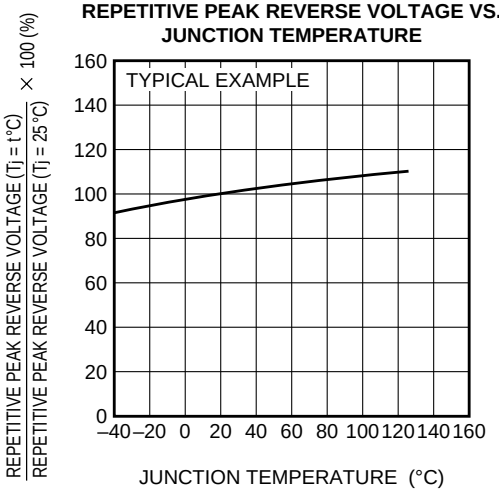
TURN-ON TIME VS. GATE CURRENT



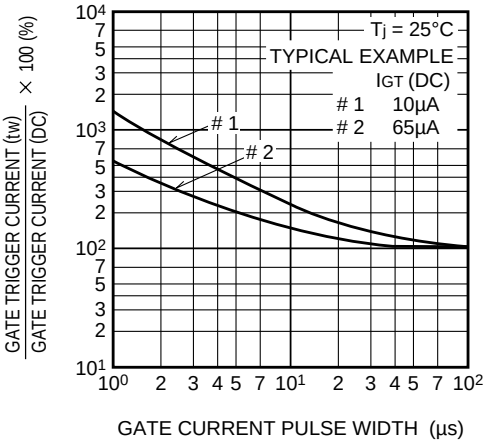
TURN-OFF TIME VS. JUNCTION TEMPERATURE



REPETITIVE PEAK REVERSE VOLTAGE VS. JUNCTION TEMPERATURE



GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH



THERMAL IMPEDANCE VS. BOARD DIMENSIONS